



ON Semiconductor®

# FGH25T120SMD

## 1200 V, 25 A Field Stop Trench IGBT

### Features

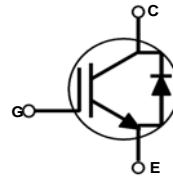
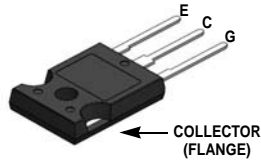
- FS Trench Technology, Positive Temperature Coefficient
- High Speed Switching
- Low Saturation Voltage:  $V_{CE(sat)} = 1.8 \text{ V @ } I_C = 25 \text{ A}$
- 100% of The Parts Tested for  $I_{LM}(1)$
- High Input Impedance
- RoHS Compliant

### General Description

Using innovative field stop trench IGBT technology, ON Semiconductor's new series of field stop trench IGBTs offer the optimum performance for hard switching application such as solar inverter, UPS, welder and PFC applications.

### Applications

- Solar Inverter, Welder, UPS & PFC Applications.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	Ratings	Unit
$V_{CES}$	Collector to Emitter Voltage	1200	V
$V_{GES}$	Gate to Emitter Voltage	$\pm 25$	V
	Transient Gate to Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	50	A
	Collector Current @ $T_C = 100^\circ\text{C}$	25	A
$I_{LM}(1)$	Clamped Inductive Load Current @ $T_C = 25^\circ\text{C}$	100	A
$I_{CM}(2)$	Pulsed Collector Current	100	A
$I_F$	Diode Continuous Forward Current @ $T_C = 25^\circ\text{C}$	50	A
	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	25	A
$I_{FM}$	Diode Maximum Forward Current	200	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	428	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	214	W
$T_J$	Operating Junction Temperature	-55 to +175	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	--	0.35	$^\circ\text{C/W}$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction to Case	--	1.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	--	40	$^\circ\text{C/W}$

**Notes:**

1.  $V_{CC} = 600 \text{ V}$ ,  $V_{GE} = 15 \text{ V}$ ,  $I_C = 100 \text{ A}$ ,  $R_G = 23 \Omega$ , Inductive Load
2. Limited by  $T_{jmax}$

FGH25T120SMD — 1200 V, 25 A Field Stop Trench IGBT

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGH25T120SMD	FGH25T120SMD-F155	TO-247G03	-	-	30

### Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 250 μA	1200	-	-	V
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V	-	-	250	μA
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0 V	-	-	±400	nA
<b>On Characteristics</b>						
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 25 mA, V <sub>CE</sub> = V <sub>GE</sub>	4.9	6.2	7.5	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V T <sub>C</sub> = 25°C	-	1.8	2.4	V
		I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 175°C	-	1.9	-	V
<b>Dynamic Characteristics</b>						
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1MHz	-	2800	-	pF
C <sub>oes</sub>	Output Capacitance		-	105	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance		-	60	-	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A, R <sub>G</sub> = 23 Ω, V <sub>GE</sub> = 15 V, Inductive Load, T <sub>C</sub> = 25°C	-	40	-	ns
t <sub>r</sub>	Rise Time		-	45	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	490	-	ns
t <sub>f</sub>	Fall Time		-	12	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	1.74	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	0.56	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	2.30	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A, R <sub>G</sub> = 23 Ω, V <sub>GE</sub> = 15 V, Inductive Load, T <sub>C</sub> = 175°C	-	40	-	ns
t <sub>r</sub>	Rise Time		-	48	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	520	-	ns
t <sub>f</sub>	Fall Time		-	64	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	2.94	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	1.09	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	4.03	-	mJ
Q <sub>g</sub>	Total Gate Charge	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V	-	225	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge		-	20	-	nC
Q <sub>gc</sub>	Gate to Collector Charge		-	128	-	nC

**Electrical Characteristics of the DIODE**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{FM}$	Diode Forward Voltage	$I_F = 25\text{ A}, T_C = 25^\circ\text{C}$	-	2.8	3.7	V
		$I_F = 25\text{ A}, T_C = 175^\circ\text{C}$	-	2.1	-	V
$t_{rr}$	Diode Reverse Recovery Time	$V_R = 600\text{ V}, I_F = 25\text{ A},$ $di_F/dt = 200\text{ A/us}, T_C = 25^\circ\text{C}$	-	60	-	ns
$I_{rr}$	Diode Peak Reverse Recovery Current		-	6.6	-	A
$Q_{rr}$	Diode Reverse Recovery Charge		-	197	-	nC
$E_{rec}$	Reverse Recovery Energy	$V_R = 600\text{ V}, I_F = 25\text{ A},$ $di_F/dt = 200\text{ A/us}, T_C = 175^\circ\text{C}$	-	330	-	$\mu\text{J}$
$t_{rr}$	Diode Reverse Recovery Time		-	325	-	ns
$I_{rr}$	Diode Peak Reverse Recovery Current		-	13	-	A
$Q_{rr}$	Diode Reverse Recovery Charge		-	2113	-	nC

## Typical Performance Characteristics

Figure 1. Typical Output Characteristics

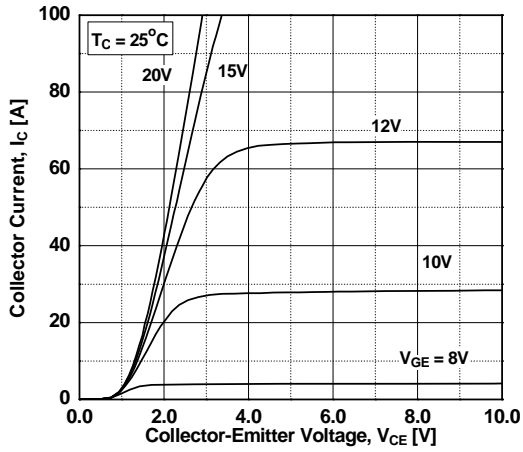


Figure 2. Typical Output Characteristics

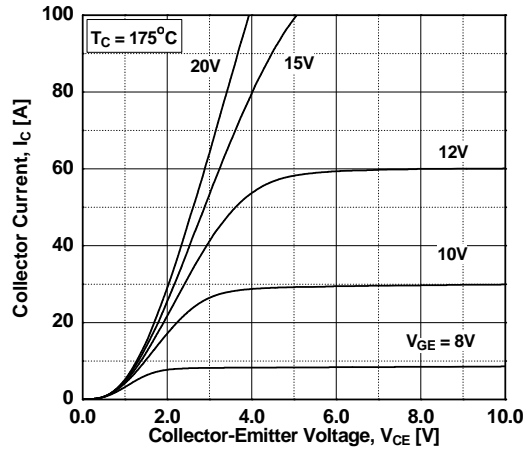


Figure 3. Typical Saturation Voltage Characteristics

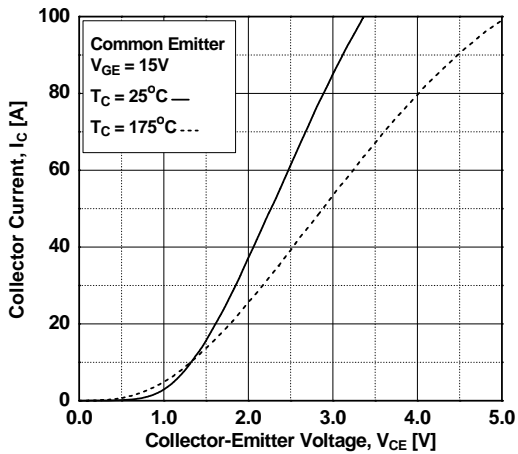


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

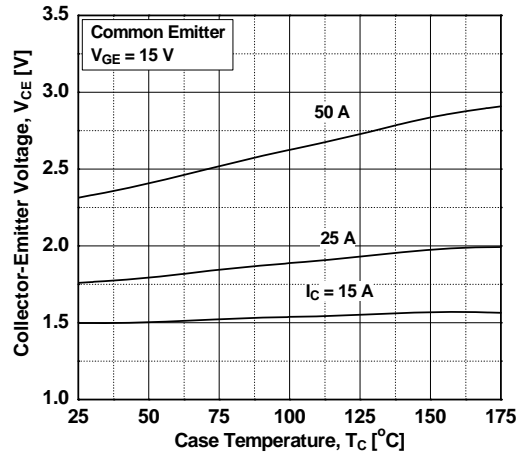


Figure 5. Saturation Voltage vs. Vge

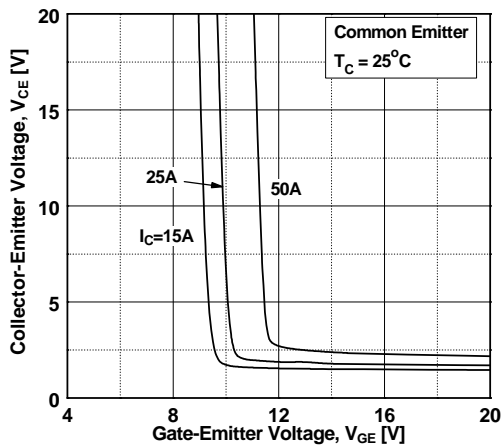
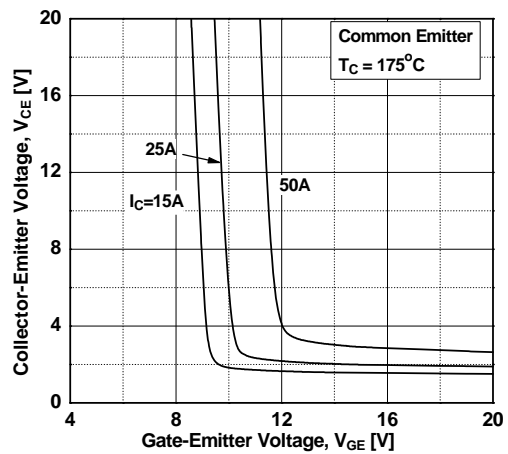
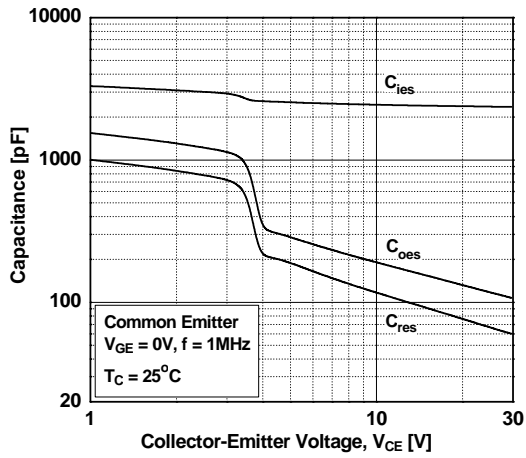


Figure 6. Saturation Voltage vs. Vge

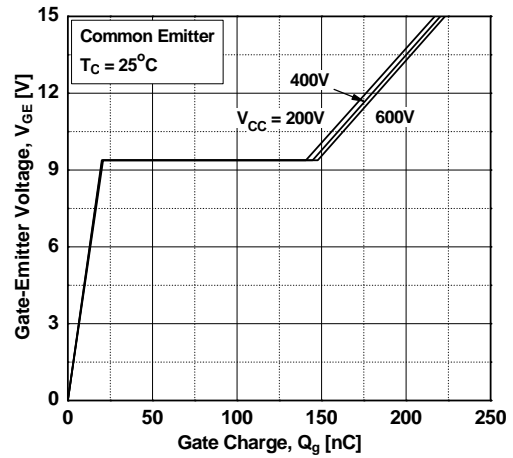


## Typical Performance Characteristics

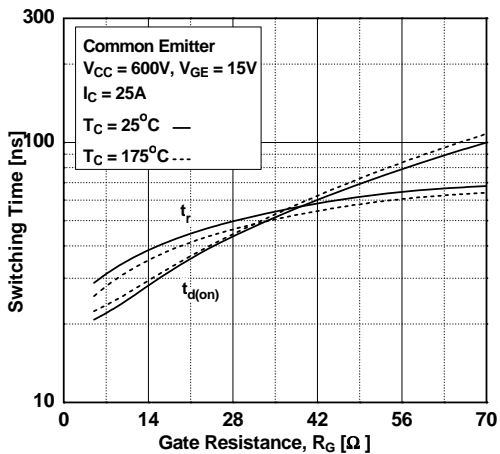
**Figure 7. Capacitance Characteristics**



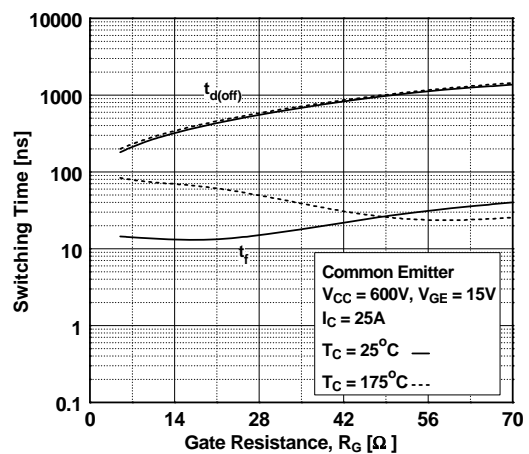
**Figure 8. Gate Charge Characteristics**



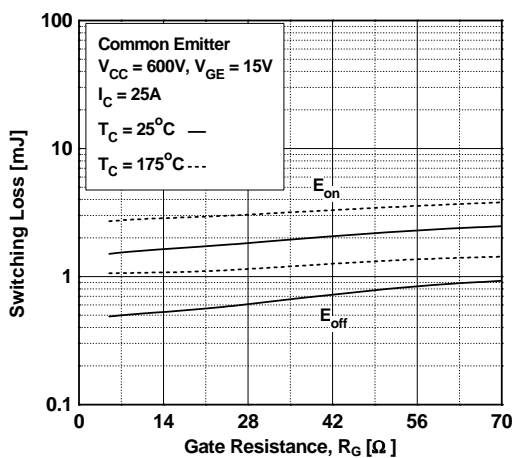
**Figure 9. Turn-on Characteristics vs. Gate Resistance**



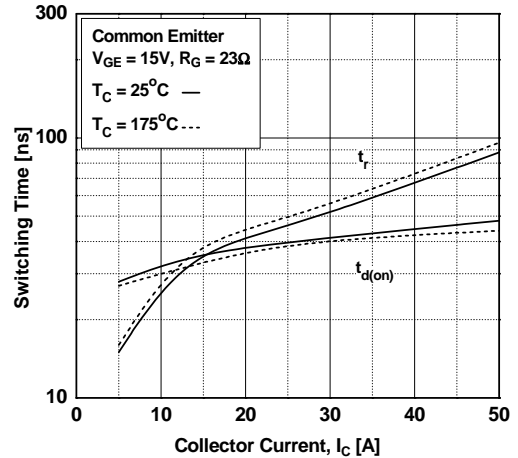
**Figure 10. Turn-off Characteristics vs. Gate Resistance**



**Figure 11. Switching Loss vs. Gate Resistance**



**Figure 12. Turn-on Characteristics vs. Collector Current**



## Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

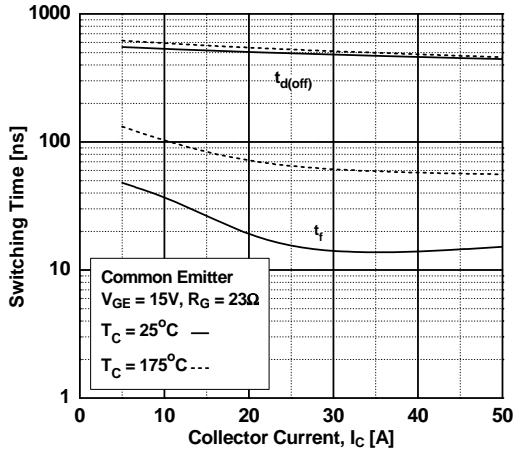


Figure 15. Load Current vs. Frequency

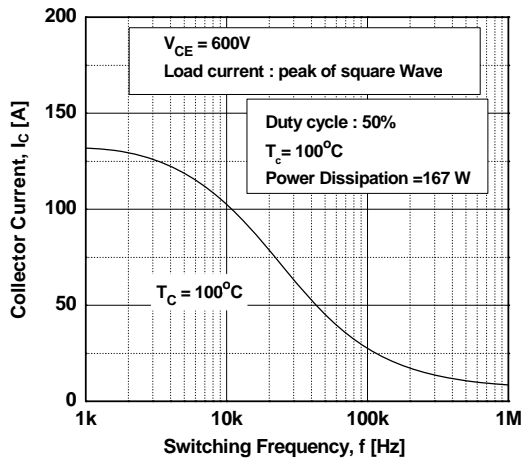


Figure 17. Forward Characteristics

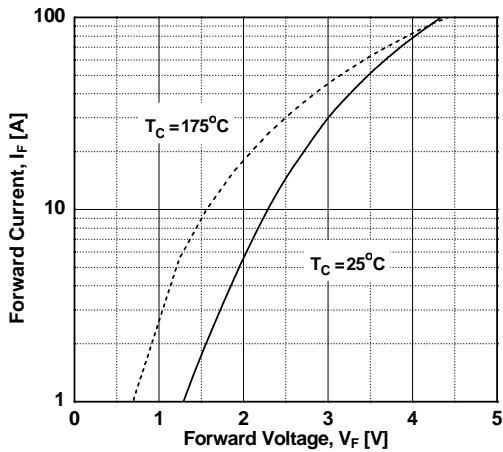


Figure 14. Switching Loss vs. Collector Current

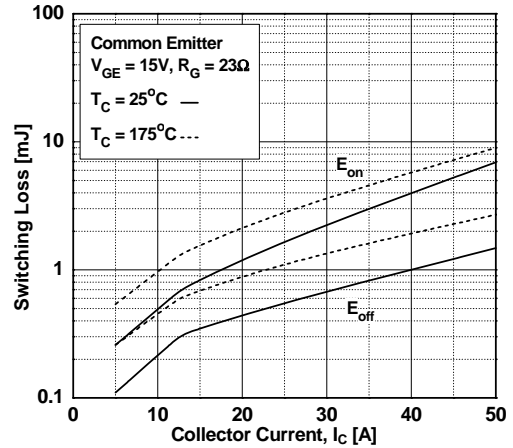


Figure 16. SOA Characteristics

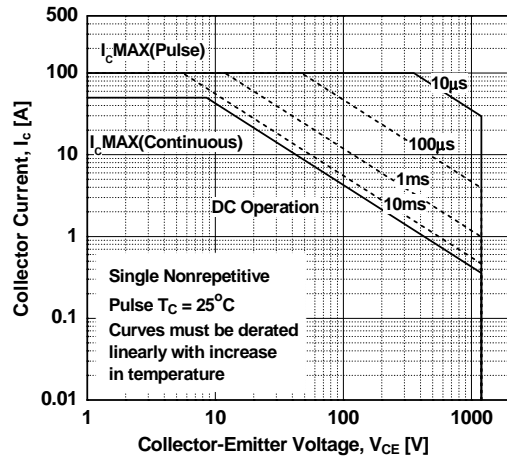
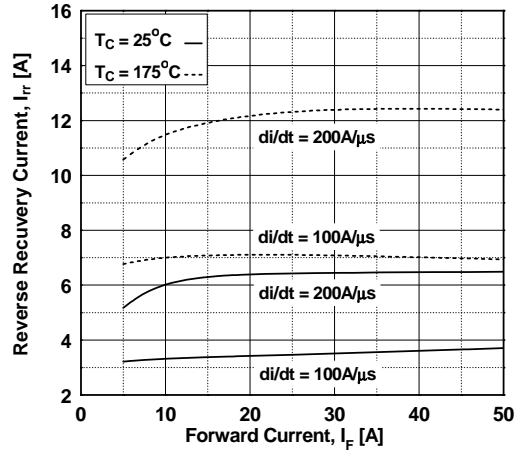


Figure 18. Reverse Recovery Current



## Typical Performance Characteristics

Figure 19. Reverse Recovery Time

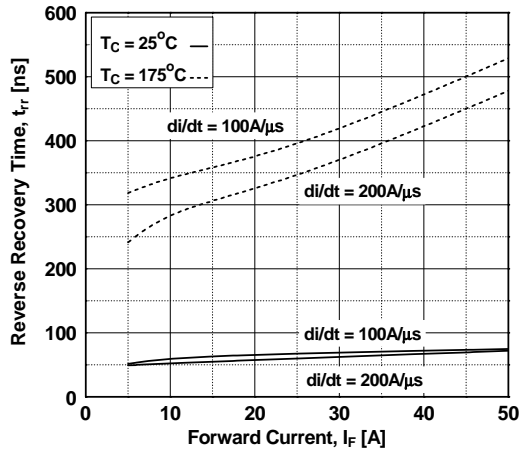


Figure 20. Stored Charge

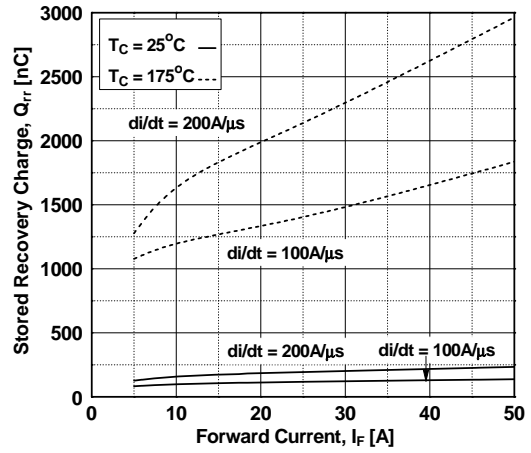


Figure 21. Transient Thermal Impedance of IGBT

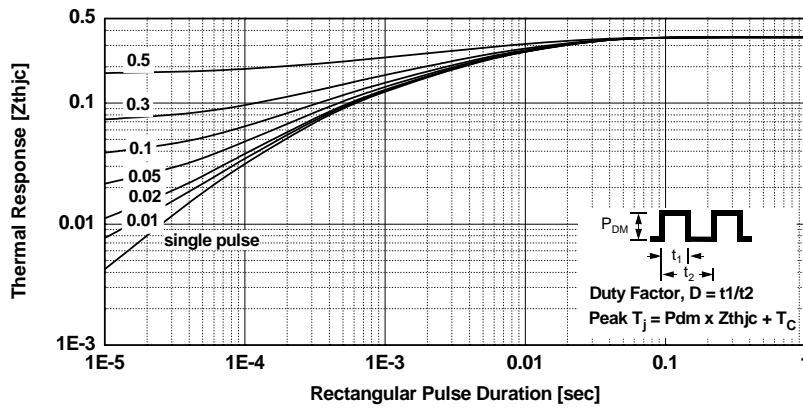
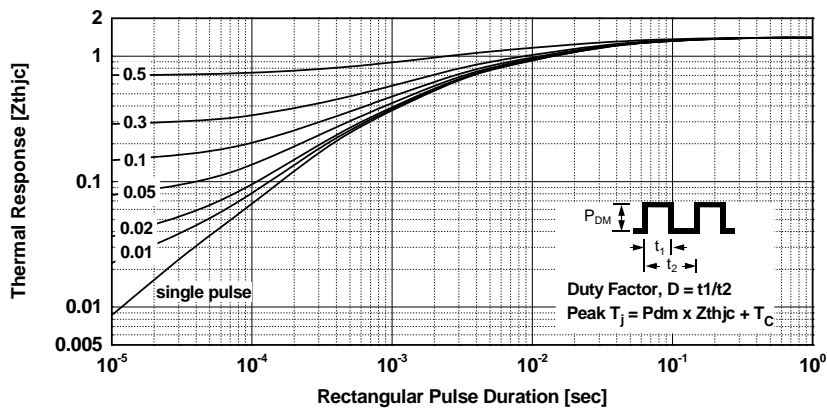
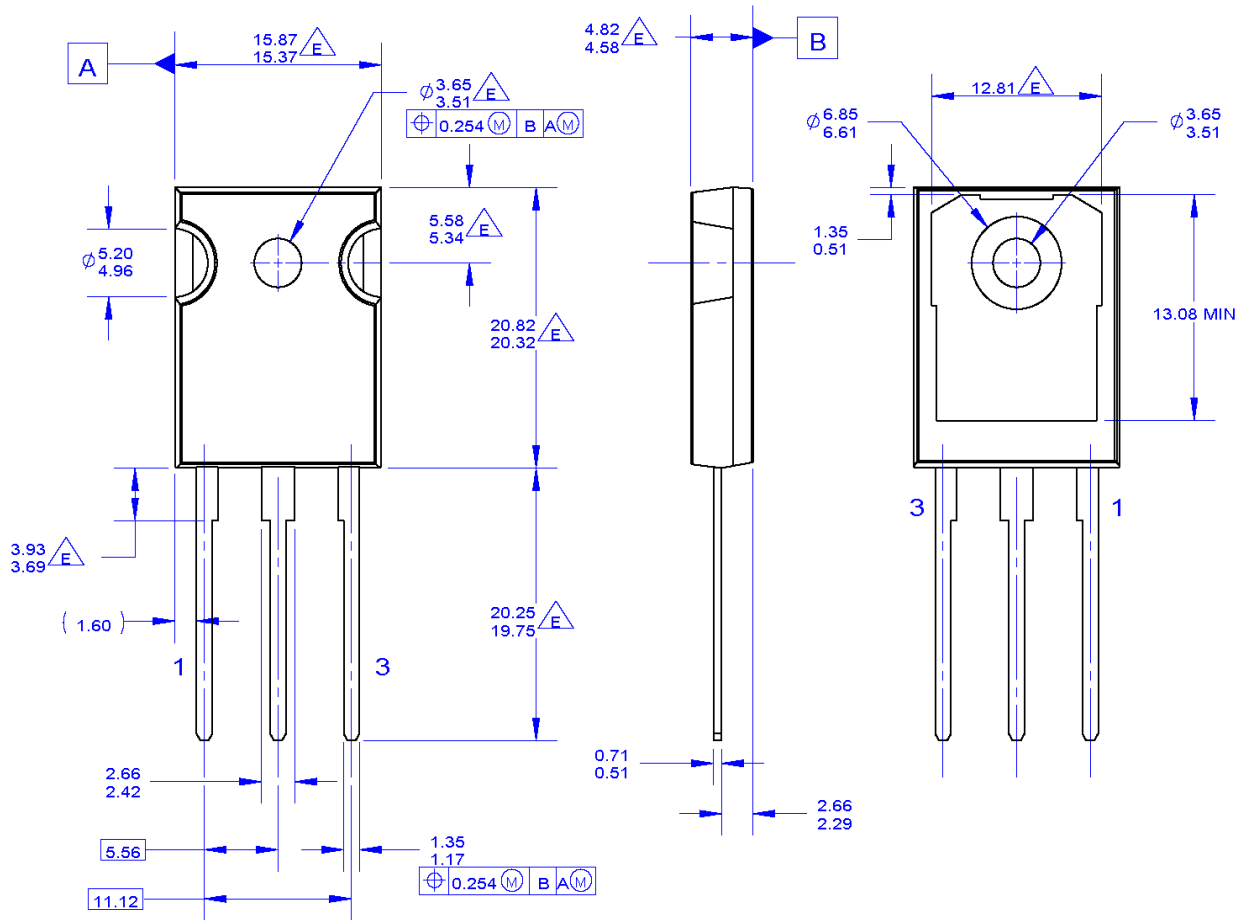


Figure 22. Transient Thermal Impedance of Diode



### Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

- DOES NOT COMPLY JEDEC STANDARD VALUE
- F. DRAWING FILENAME: MKT-TO247G03\_REV01

**Figure 23. TO-247, MOLDED, 3 LEAD, JEDEC AB LONG LEADS (Active)**

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Dimensions in Millimeters



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